54ABT16245 16-Bit Transceiver with TRI-STATE[®] Outputs

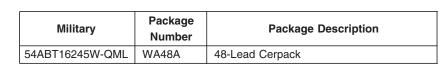
General Description

The 'ABT16245 contains sixteen non-inverting bidirectional buffers with TRI-STATE outputs and is intended for bus oriented applications. The device is byte controlled. Each byte has separate control inputs which can be shorted together for full 16-bit operation. The T/\overline{R} inputs determine the direction of data flow through the device. The \overline{OE} inputs disable both the A and B ports by placing them in a high impedance state.

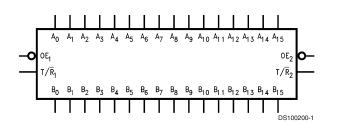
- Separate control logic for each byte
- 16-bit version of the 'ABT245
- A and B output sink capability of 48 mA, source capability of 24 mA
- Guaranteed latchup protection
- High impedance glitch free bus loading during entire power up and power down cycle
- Non-destructive hot insertion capability
- Standard Microcircuit Drawing (SMD) 5962-9317501

Features

Bidirectional non-inverting buffers



Logic Symbol



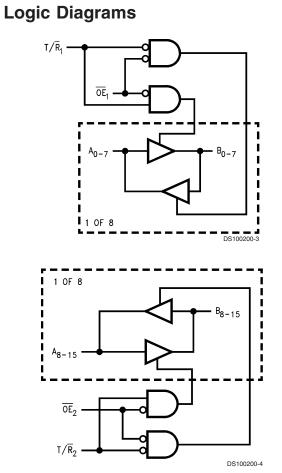
Pin Description

Pin Names	Description	
ŌĒn	Output Enable Input (Active Low)	
T/R _n	Transmit/Receive Input	
A ₀ -A ₁₅	Side A Inputs/Outputs	
B ₀ -B ₁₅	Side B Inputs/Outputs	

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Connection Diagram

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1		5		1
⊺/R ₁ —	1	Ŭ	48	- 0E1
в _о —	2		47	— A ₀
в1 —	3		46	— A ₁
gnd 🗕	4		45	— GND
в ₂ —	5		44	- A2
В ₃ —	6		43	— A3
v _{cc} –	7		42	— v _{cc}
в ₄ —	8		41	- A4
в ₅ —	9		40	— A ₅
GND —	10		39	— GND
в ₆ —	11		38	— A ₆
В ₇ —	12		37	- A7
в ₈ —	13		36	— A ₈
в ₉ —	14		35	— A ₉
gnd —	15		34	— GND
B ₁₀ —	16		33	— A ₁₀
B ₁₁ —	17		32	— A ₁₁
v _{cc} –	18		31	— v _{cc}
B ₁₂ —	19		30	— A ₁₂
B ₁₃ —	20		29	— A ₁₃
gnd —	21		28	— GND
B ₁₄ —	22		27	— A ₁₄
B ₁₅ —	23		26	— A ₁₅
T/\overline{R}_2	24		25	- OE ₂
-				
			DS1	00200-2



Functional Description

The 'ABT16245 contains sixteen non-inverting bidirectional buffers with TRI-STATE outputs. The device is byte controlled with each byte functioning identically, but independent of the other. The control pins can be shorted together to obtain full 16-bit operation.

Inputs		Outputs
OE ₁	T/R₁	
L	L	Bus $B_0 - B_7$ Data to Bus $A_0 - A_7$
L	Н	Bus $A_0 - A_7$ Data to Bus $B_0 - B_7$
Н	Х	HIGH-Z State on A ₀ -A ₇ , B ₀ -B ₇
Inputs		Outputs
\overline{OE}_2 T/ \overline{R}_2		
L	L	Bus $B_8 - B_{15}$ Data to Bus $A_8 - A_{15}$
L	Н	Bus $A_8 - A_{15}$ Data to Bus $B_8 - B_{15}$
н	Х	HIGH-Z State on A ₈ -A ₁₅ , B ₈ -B 15

H = High Voltage Level L = Low Voltage Level

X = Immaterial

Z = High Impedance

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Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Storage Temperature	-65°C to +150°C
Ambient Temperature under Bias	–55°C to +125°C
Junction Temperature under Bias	
Ceramic	–55°C to +175°C
V _{CC} Pin Potential to	
Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output	
in the Disabled or	
Power-off State	-0.5V to 5.5V
in the HIGH State	–0.5V to $V_{\rm CC}$

Current Applied to Output in LOW State (Max) twice the DC Latchup Source Current Over Voltage Latchup (I/O)

twice the rated $I_{OL}~(mA)$ -500~mA 10V

Recommended Operating Conditions

Free Air Ambient Temperature	
Military	–55°C to +125°C
Supply Voltage	
Military	+4.5V to +5.5V
Minimum Input Edge Rate	$(\Delta V/\Delta t)$
Data Input	50 mV/ns
Enable Input	20 mV/ns
Note 1: Absolute maximum ratings are values bey	rond which the device may

be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol	Parameter		ABT16245		Units	V _{cc}	Conditions
			Min	Тур Мах	1		
V _{IH}	Input HIGH Voltage		2.0		V		Recognized HIGH Signal
V _{IL}	Input LOW Voltage			0.8	V		Recognized LOW Signal
V _{CD}	Input Clamp Diode Vo	ltage		-1.2	V	Min	$I_{IN} = -18 \text{ mA} (\overline{OE}_n, \text{ T/R}_n)$
V _{OH}	Output HIGH Voltage	54ABT	2.5		V	Min	$I_{OH} = -3 \text{ mA} (A_n, B_n)$
		54ABT	2.0		V	Min	$I_{OH} = -24 \text{ mA} (A_n, B_n)$
V _{OL}	Output LOW Voltage	54ABT		0.55	V	Min	$I_{OL} = 48 \text{ mA} (A_n, B_n)$
I _{IH}	Input HIGH Current			5	μA	Max	$V_{IN} = 2.7V \ (\overline{OE}_n, T/\overline{R}_n) \ (Note 3)$
				5			$V_{IN} = V_{CC} (\overline{OE}_n, T/\overline{R}_n)$
I _{BVI}	Input HIGH Current			7	μA	Max	$V_{IN} = 7.0V \ (\overline{OE}_n, T/\overline{R}_n)$
	Breakdown Test						
I _{BVIT}	Input HIGH Current			100	μA	Max	$V_{IN} = 5.5V (A_n, B_n)$
	Breakdown Test (I/O)						
I _{IL}	Input LOW Current			-5	μA	Max	$V_{IN} = 0.5V \ (\overline{OE}_n, T/\overline{R}_n) \ (Note 3)$
				-5			$V_{IN} = 0.0V \ (\overline{OE}_n, T/\overline{R}_n)$
V _{ID}	Input Leakage Test		4.75		V	0.0	$I_{ID} = 1.9 \ \mu A \ (\overline{OE}_n, \ T/\overline{R}_n)$
							All Other Pins Grounded
I _{IH} + I	Output Leakage Curre	ent		50	μA	0 -	$V_{OUT} = 2.7V (A_n, B_n); \overline{OE} = 2.0V$
OZH						5.5V	
I _{IL} + I	Output Leakage Curre	ent		-50	μA	0 -	$V_{OUT} = 0.5V (A_n, B_n); \overline{OE} = 2.0V$
OZL						5.5V	
l _{os}	Output Short-Circuit C		-100	-275	mA	Max	$V_{OUT} = 0.0V (A_n, B_n)$
I _{CEX}	Output High Leakage	Current		50	μA	Max	$V_{OUT} = V_{CC} (A_n, B_n)$
I _{ZZ}	Bus Drainage Test			100	μA	0.0	$V_{OUT} = 5.50V (A_n, B_n);$
							All Others GND
I _{ссн}	Power Supply Current			100	μA	Max	All Outputs HIGH
I _{CCL}	Power Supply Current			60	mA	Max	All Outputs LOW
I _{CCZ}	Power Supply Current			100	μA	Max	$\overline{OE}_n = V_{CC}, T/\overline{R}_n = GND \text{ or } V_{CC}$
							All others at V _{CC} or GND
I _{CCT}	Additional I _{CC} /Input	Outputs Enabled		2.5	mA		$V_{I} = V_{CC} - 2.1V$
		Outputs TRI-STATE		2.5	mA	Max	\overline{OE}_n , T/ \overline{R}_n V _I = V _{CC} – 2.1V
		Outputs TRI-STATE		50	μA		Data Input $V_I = V_{CC} - 2.1V$
							All others at V_{CC} or GND

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DC Electrical Characteristics (Continued)

Symbol	Parameter		Parameter ABT16245		V _{cc}	Conditions	
			Min Typ Max				
I _{CCD}	Dynamic I _{CC}	No Load		mA/	Max	Outputs Open	
			0.1	MHz		$\overline{OE}_n = GND, T/\overline{R}_n = GND \text{ or } V_{CC}$	
						One Bit Toggling, 50% Duty Cycle	

Note 3: Guaranteed, but not tested.

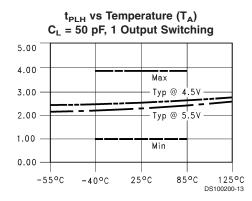
AC Electrical Characteristics

Symbol	Parameter	54ABT T _A = -55°C to +125°C V _{CC} = 4.5V–5.5V C _L = 50 pF		Units	Fig.
				–55°C to +125°C V _{CC} = 4.5V−5.5V	
	-	Min	Max	-	
t _{PLH}	Propagation	0.5	4.5		
t _{PHL}	Delay Data	0.5	5.2	ns	Figure 5
	to Outputs				
t _{PZH}	Output Enable	0.8	6.4	ns	Figure 4
t _{PZL}	Time	0.9	6.9		
t _{PHZ}	Output Disable	1.3	6.9	ns	Figure 4
t _{PLZ}	Time	1.0	6.9		

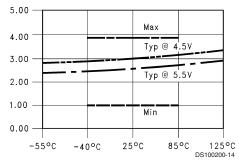
Capacitance

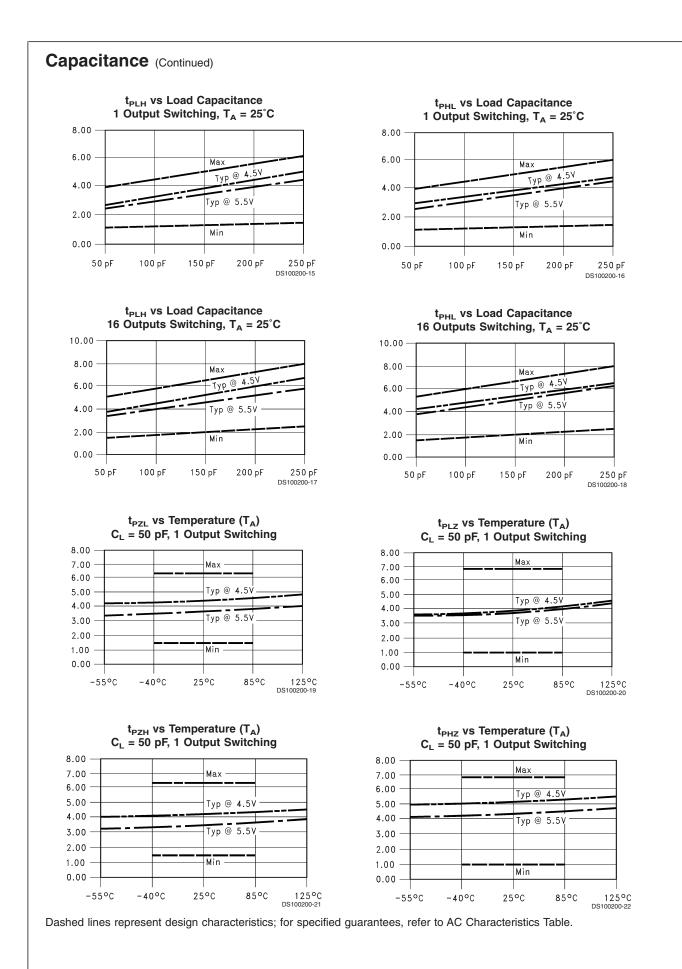
Symbol	Parameter	Тур	Units	Conditions, T _A = 25°C
C _{IN}	Input Capacitance	5	pF	$V_{CC} = 0.0V \ (\overline{OE}_n, T/\overline{R}_n)$
C _{I/O} (Note 4)	Output Capacitance	11	pF	$V_{\rm CC} = 5.0V (A_{\rm n}, B_{\rm n})$

Note 4: $C_{I/O}$ is measured at frequency f = 1 MHz, per MIL-STD-883B, Method 3012.



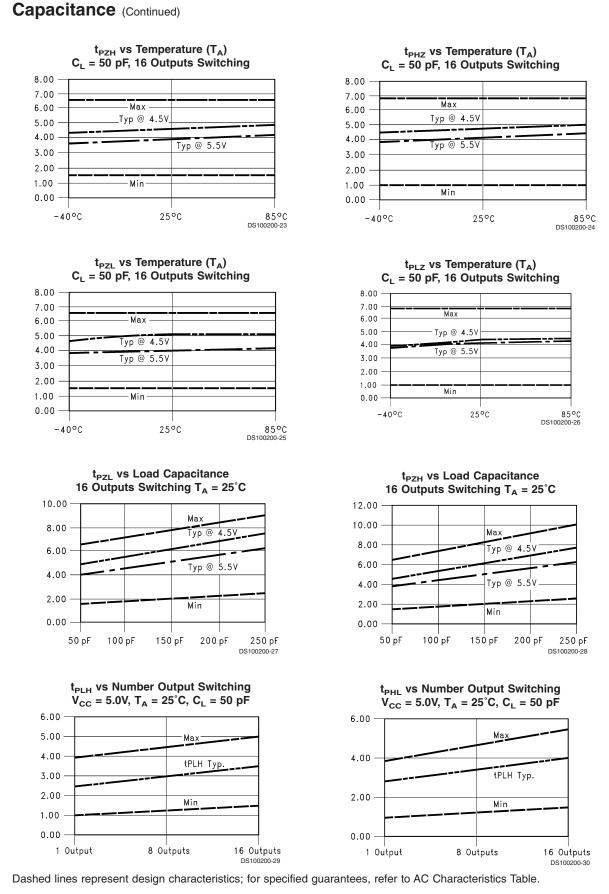
t_{PHL} vs Temperature (T_A) C_L = 50 pF, 1 Output Switching

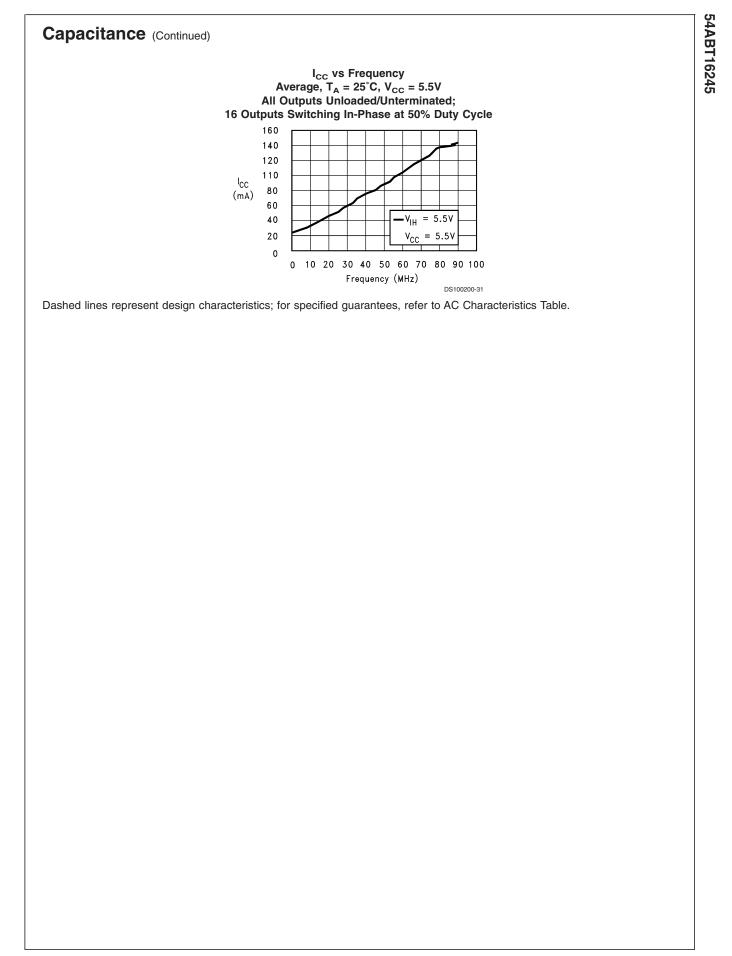




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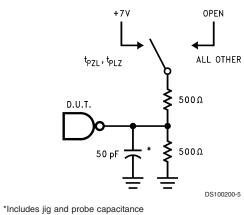






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AC Loading



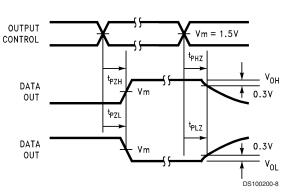


FIGURE 4. TRI-STATE Output HIGH and LOW Enable and Disable Times

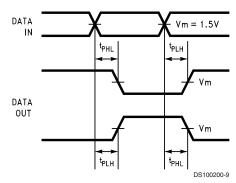


FIGURE 5. Propagation Delay Waveforms for Inverting and Non-Inverting Functions

FIGURE 1. Standard AC Test Load

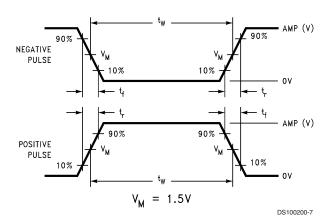
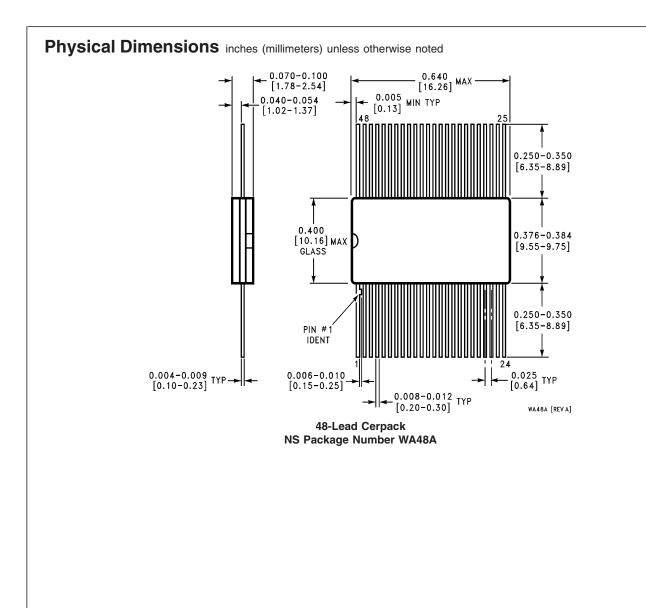


FIGURE 2. Input Pulse Requirements

Amplitude	Rep. Rate	t _w	t _r	t _f
3.0V	1 MHz	500 ns	2.5 ns	2.5 ns

FIGURE 3. Test Input Signal Requirements



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